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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: William J. Schaff et al.

Title: AIN COATED HETEROJUNCTION FIELD EFFECT TRANSISTOR AND METHOD OF FORMING AN AIN COATING

Docket No.: 1153.044US1

Filed: May 15, 2001

Examiner: Khanh Duong

Serial No.: 09/858,337

Due Date: September 10, 2002

Group Art Unit: 2822

Commissioner for Patents
Washington, D.C. 20231

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We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ An Amendment and Response Under 37 C.F.R. 1.111 (5 Pages).
- ☒ Clean Version of Pending Claims (4 pgs.).
- ☒ Clean Version of Amended Specification Paragraphs (1 pg.).

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 10th day of September, 2002.

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S/N 09/858,337

PATENT

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Applicant: William J. Schaff et al. Examiner: Khanh Duong
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3/A Amold
9/24/02
A. Walker

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on June 10, 2002. Please amend the above-identified patent application as follows.

IN THE SPECIFICATION

Please make the paragraph substitutions indicated in the appendix entitled Clean Version of Amended Specification Paragraphs. The specific changes incorporated in the substitute paragraphs are shown in the following marked-up versions of the original paragraphs:

The paragraph beginning at page 2, line 7 is amended as follows:

There is a need for increasing the power output of HFETs. Prior attempts include using a layer of [Si₃N₄] Si₃N₄ over the surface of an already formed HFET. While this improved the power output of the HFET, it required different equipment than was used to form the HFET. Further, controlling the ratios of the deposition required careful calibration and it was difficult to obtain consistent results.

It is believed that the amendment to the specification above obviates the Examiner's objection to the specification as outlined on page 3 of the Office Action.

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